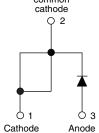


Vishay Semiconductors

# Hyperfast Rectifier, 30 A FRED Pt®





TO-247AC modified

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Cathode	Anode

PRODUCT SUMMARY					
Package	TO-247AC modified (2 pins)				
I <sub>F(AV)</sub>	30 A				
$V_{R}$	600 V				
V <sub>F</sub> at I <sub>F</sub>	2.6 V				
t <sub>rr</sub> typ.	See Recovery table				
T <sub>J</sub> max.	175 °C				
Diode variation	Single die				

#### **FEATURES**

- · Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Single diode device
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)





# HALOGEN FREE

### **DESCRIPTION/APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	$V_{RRM}$		600	V		
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 116 °C	30	^		
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	300	A		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 30 A	-	2.0	2.6	V	
		I <sub>F</sub> = 30 A, T <sub>J</sub> = 150 °C	-	1.34	1.75		
Payaraa laakaga aurrant	1	V <sub>R</sub> = V <sub>R</sub> rated	-	0.3	50		
Reverse leakage current I <sub>R</sub>		$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	60	500	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	33	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	3.5	-	nH	



# **VS-30EPH06PbF, VS-30EPH06-N3**

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		28	35		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	31	-	ns	
		T <sub>J</sub> = 125 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	77	-		
Dools woods on the out	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	3.5	-	^	
Peak recovery current		T <sub>J</sub> = 125 °C		-	7.7	-	A	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	65	-	200	
		T <sub>J</sub> = 125 °C		-	345	=	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C	
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	0.5	0.9		
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.4	-		
Weight			-	6.0	-	g	
vveignt			-	0.22	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC modified		30EPH06			



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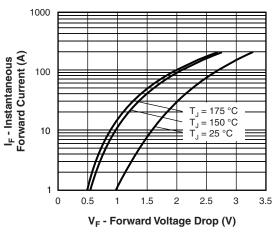


Fig. 1 - Typical Forward Voltage Drop Characteristics

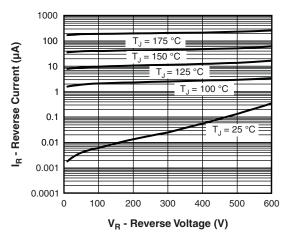


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

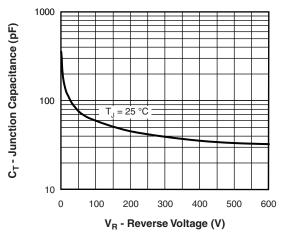


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

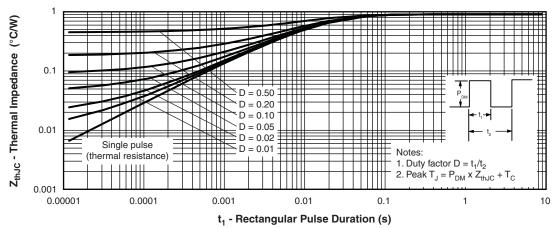


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics





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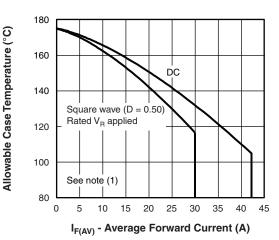


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

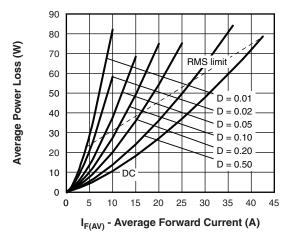


Fig. 6 - Forward Power Loss Characteristics

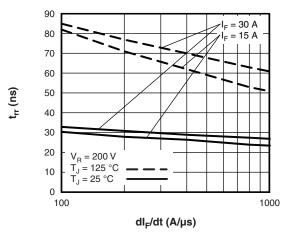


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

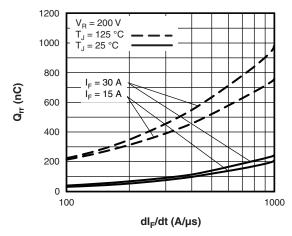


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{l} \text{(1)} \ \ \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$ 

## Vishay Semiconductors

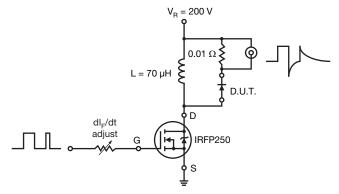
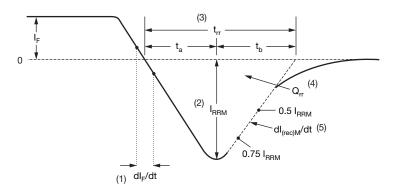


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

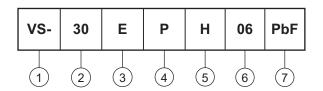
Fig. 10 - Reverse Recovery Waveform and Definitions

# **VS-30EPH06PbF, VS-30EPH06-N3**

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### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (30 = 30 A)

3 - Circuit configuration:

E = Single diode

4 - Package:

P = TO-247AC modified

5 - H = Hyperfast recovery

6 - Voltage rating (06 = 600 V)

7 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

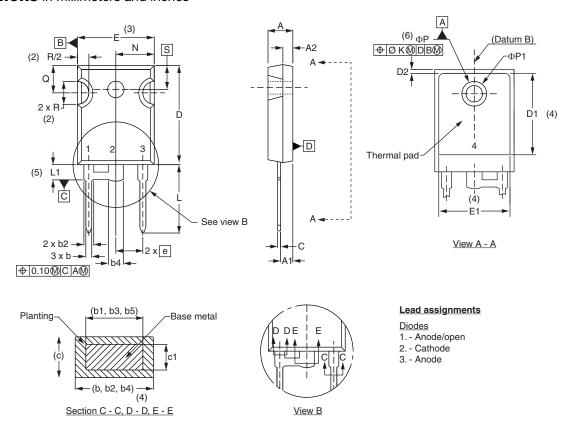
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-30EPH06PbF	25	500	Antistatic plastic tube				
VS-30EPH06-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95253			
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255			
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442			



## Vishay Semiconductors

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.37	0.065	0.094	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.86	0.015	0.034	
c1	0.38	0.76	0.015	0.030	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	1	
е	5.46	BSC	0.215	BSC	
ΦК	2.	54	0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0	.3	
ΦР	3.56	3.66	0.14	0.144	
ФР1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	1.78	0.216	
S	5.51	BSC	0.217	BSC	

#### Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6)  $\Phi P$  to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



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